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Sheet	A1	of	A1
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First Named Inventor	Gerald Lucovsky
Confirmation No.	3119
Examiner Name	Benjamin P. Sandvik
Attorney Docket Number	5051-639

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OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	2.	Woo Sik Kim; Ferroelectric-gate field effect transistors using Nd₂TiO₇/Y₂O₃/Si structures; Thin Solid Films 398-399 (2001) 663-667.	
	3.	Seung-Gu Lim; Dielectric functions and optical bandgaps of high-K dielectrics for metal-oxide-semiconductor field-effect transistors by far ultraviolet spectroscopic ellipsometry; Journal of Applied Physics, Volume: 91, Number 7, pp 4500-4505 (April 1, 2002).	
	4.	J.K. Yamamoto; Microwave dielectric properties of layered perovskite A₂B₂O₇ single-crystal fibers; Elsevier Science Publishers B.V. (North-Holland (1991) Material Letters No. 11/12 pp 497-500.	
	5.	European communication with European Search Report for Application No. 04776548.2 – 1235 PCT/US2004018863, dated 5-6-2008.	

Date Considered

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